50 mA Ultra-Low Iq, Wide Input Voltage, Low Dropout Linear Voltage Regulator

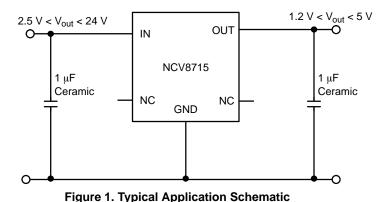
The NCV8715 is 50 mA LDO Linear Voltage Regulator. It is a very stable and accurate device with ultra–low ground current consumption (4.7 μ A over the full output load range) and a wide input voltage range (up to 24 V). The regulator incorporates several protection features such as Thermal Shutdown and Current Limiting.

Features

- Operating Input Voltage Range: 2.5 V to 24 V
- Fixed Voltage Options Available: 1.2 V to 5.0 V
- Ultra Low Quiescent Current: Max. 5.8 μA Over Full Load and Temperature
- ±2% Accuracy Over Full Load, Line and Temperature Variations
- PSRR: 52 dB at 100 kHz
- Noise: 190 μV_{RMS} from 200 Hz to 100 kHz
- Thermal Shutdown and Current Limit protection
- Available in XDFN6 1.5 x 1.5 mm and SC-70 (SC-88A) Package
- These are Pb-Free Devices

Typical Applications

- Infotainment, Audio
- Communication Systems
- Safety Systems





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SC-70-5 (SC-88A) CASE 419A



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 19 of this data sheet.

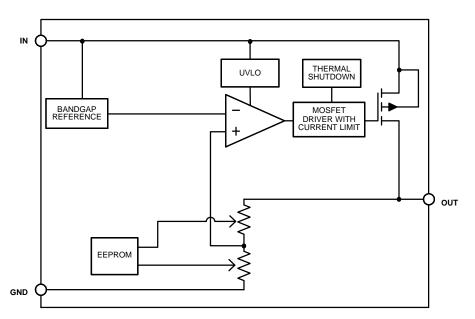


Figure 2. Simplified Block Diagram



Figure 3. Pin Description

PIN FUNCTION DESCRIPTION

| Pin No. | | | |
|---------|---------------|-----|---|
| SC-70 | XDFN6 Pin Nan | | Description |
| 5 | 6 | OUT | Regulated output voltage pin. A small 0.47 μF ceramic capacitor is needed from this pin to ground to assure stability. |
| 1 | 2 | N/C | No connection. This pin can be tied to ground to improve thermal dissipation or left disconnected. |
| 2 | 3 | GND | Power supply ground. |
| 3 | 4 | N/C | No connection. This pin can be tied to ground to improve thermal dissipation or left disconnected. |
| - | 5 | N/C | No connection. This pin can be tied to ground to improve thermal dissipation or left disconnected. |
| 4 | 1 | IN | Input pin. A small capacitor is needed from this pin to ground to assure stability. |

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|--------------------|------------|------|
| Input Voltage (Note 1) | V _{IN} | -0.3 to 24 | V |
| Output Voltage | V _{OUT} | -0.3 to 5 | V |
| Output Short Circuit Duration | t _{SC} | Indefinite | S |
| Maximum Junction Temperature | $T_{J(MAX)}$ | 125 | °C |
| Storage Temperature | T _{STG} | -55 to 150 | °C |
| Moisture Sensitivity Level | MSL | MSL1 | - |
| ESD Capability, Human Body Model (Note 2) | ESD _{HBM} | 2000 | V |
| ESD Capability, Machine Model (Note 2) | ESD _{MM} | 200 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

2. This device series incorporates ESD protection and is tested by the following methods:

- - ESD Human Body Model tested per AEC-Q100-002 (EIA/JESD22-A114)
 - ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115)
 Latch up Current Maximum Rating tested per JEDEC standard: JESD78.

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|--|----------------|-------|------|
| Thermal Characteristics, SC–70 (Note 3) Thermal Resistance, Junction–to–Air (Note 4) | $R_{	heta JA}$ | 390 | °C/W |
| Thermal Characteristics, XDFN6 (Note 3) Thermal Resistance, Junction–to–Air (Note 4) | $R_{	heta JA}$ | 260 | °C/W |

- 3. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
- 4. As measured using a copper heat spreading area of 650 mm², 1 oz copper thickness.

ELECTRICAL CHARACTERISTICS – Voltage Version 1.2 V

 $-40^{\circ}\text{C} \le \text{T}_{\text{J}} \le 125^{\circ}\text{C}; \text{V}_{\text{IN}} = 2.5 \text{ V}; \text{I}_{\text{OUT}} = 1 \text{ mA}, \text{C}_{\text{IN}} = \text{C}_{\text{OUT}} = 1.0 \,\mu\text{F}, \text{unless otherwise noted.}$ Typical values are at T_J = +25°C. (Note 7)

| Parameter | Test Conditions | Symbol | Min | Тур | Max | Unit |
|---------------------------------------|---|---------------------|-------|-----|-------|---------------|
| Operating Input Voltage | I _{OUT} ≤ 10 mA | V _{IN} | 2.5 | | 24 | V |
| | 10 mA< I _{OUT} < 50 mA | | 3.0 | | 24 | 1 |
| Output Voltage Accuracy | 3.0 V < V _{IN} < 24 V, 0 mA < I _{OUT} < 50 m | A V _{OUT} | 1.164 | 1.2 | 1.236 | V |
| Line Regulation | $2.5 \text{ V} \le \text{V}_{\text{IN}} \le 24 \text{ V}, \text{I}_{\text{OUT}} = 1 \text{ mA}$ | Reg _{LINE} | | 2 | 10 | mV |
| Load Regulation | I _{OUT} = 0 mA to 50 mA | Reg _{LOAD} | | 5 | 10 | mV |
| Dropout Voltage (Note 5) | | V_{DO} | | | _ | mV |
| Maximum Output Current | (Note 8) | l _{OUT} | 100 | | 200 | mA |
| | 0 < I _{OUT} < 50 mA, V _{IN} = 24 V | I _{GND} | | 3.4 | 5.8 | |
| Power Supply Rejection Ratio | $ \begin{array}{c} V_{IN} = 3.0 \text{ V, } V_{OUT} = 1.2 \text{ V} \\ V_{PP} = 200 \text{ mV modulation} \\ I_{OUT} = 1 \text{ mA, } C_{OUT} = 10 \mu\text{F} \end{array} $ | Hz PSRR | | 60 | | dB |
| Output Noise Voltage | V_{OUT} = 1.2 V, I_{OUT} = 50 mA f = 200 Hz to 100 kHz, C_{OUT} = 10 μ F | V _N | | 65 | | μV_{rms} |
| Thermal Shutdown Temperature (Note 6) | Temperature increasing from T _J = +25° | C T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 6) | Temperature falling from T _{SD} | T _{SDH} | _ | 15 | _ | °C |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Not Characterized at V_{IN} = 3.0 V, V_{OUT} = 1.2 V, I_{OUT} = 50 mA.

6. Guaranteed by design and characterization.

^{7.} Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at $T_J = T_A = T_A$ 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

^{8.} Respect SOA.

ELECTRICAL CHARACTERISTICS – Voltage Version 1.5 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 2.5 \text{ V}$; $I_{OUT} = 1 \text{ mA}$, $C_{IN} = C_{OUT} = 1.0 \ \mu\text{F}$, unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 11)

| Parameter | Test Conditions | | Symbol | Min | Тур | Max | Unit |
|--|---|---|---------------------|-------|-----|-------|-------------------|
| Operating Input Voltage | I _{OUT} ≤ 10 mA | | V _{IN} | 2.5 | | 24 | V |
| | 10 mA < I _{OUT} < 50 i | mA | | 3.0 | | 24 | |
| Output Voltage Accuracy | 3.0 V < VIN < 24 V, 0 < I _{OU} | _C < 50 mA | V _{OUT} | 1.455 | 1.5 | 1.545 | V |
| Line Regulation | Vout + 1 V ≤ Vin ≤ 24 V, I _O | _{UT} = 1 mA | Reg _{LINE} | | 2 | 10 | mV |
| Load Regulation | I _{OUT} = 0 mA to 50 r | nA | Reg _{LOAD} | | 5 | 10 | mV |
| Dropout Voltage (Note 9) | | | V_{DO} | | | - | mV |
| Maximum Output Current | (Note 12) | (Note 12) | | 100 | | 200 | mA |
| Ground Current | 0 < I _{OUT} < 50 mA, V _{IN} : | = 24 V | I _{GND} | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $\begin{aligned} &V_{IN} = 3.0 \text{ V, } V_{OUT} = 1.5 \text{ V} \\ &V_{PP} = 200 \text{ mV modulation} \\ &I_{OUT} = 1 \text{ mA, } C_{OUT} = 10 \mu\text{F} \end{aligned}$ | f = 100 kHz | PSRR | | 56 | | dB |
| Output Noise Voltage | V _{OUT} = 1.5 V, I _{OUT} = 5 f = 200 Hz to 100 kHz, C _{OU} | V _{OUT} = 1.5 V, I _{OUT} = 50 mA f = 200 Hz to 100 kHz, C _{OUT} = 10 μF | | | 75 | | μV _{rms} |
| Thermal Shutdown Temperature (Note 10) | Temperature increasing from T _J = +25°C | | T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 10) | Temperature falling from | m T _{SD} | T _{SDH} | _ | 15 | _ | °C |

 ^{9.} Not Characterized at V_{IN} = 3.0 V, V_{OUT} = 1.5 V, I_{OUT} = 50 mA.
 10. Guaranteed by design and characterization.
 11. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 12. Respect SOA.

ELECTRICAL CHARACTERISTICS – Voltage Version 1.8 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 2.8V$; $I_{OUT} = 1$ mA, $C_{IN} = C_{OUT} = 1.0$ μF , unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 15)

| Parameter | Test Conditions | 1 | Symbol | Min | Тур | Max | Unit |
|--|--|---|---------------------|-------|-----|-------|-------------------|
| Operating Input Voltage | Iout ≤10 mA | Iout ≤10 mA | | 2.8 | | 24 | V |
| | 10 mA < I _{OUT} < 50 | 10 mA < I _{OUT} < 50 mA | | 3.0 | | 24 | |
| Output Voltage Accuracy | 3.0 V < V _{IN} < 24 V, 0 < I _{OU} | _T < 10 mA | V _{OUT} | 1.746 | 1.8 | 1.854 | V |
| Line Regulation | 3 V ≤ VIN ≤ 24 V, I _{OUT} = | = 1 mA | Reg _{LINE} | | 2 | 10 | mV |
| Load Regulation | $I_{OUT} = 0$ mA to 50 r | mA | Reg _{LOAD} | | 5 | 10 | mV |
| Dropout Voltage (Note 13) | | | V_{DO} | | | | mV |
| Maximum Output Current | (Note 16) | (Note 16) | | 100 | | 200 | mA |
| Ground Current | 0 < I _{OUT} < 50 mA, V _{IN} | = 24 V | I _{GND} | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $\begin{aligned} &V_{\text{IN}} = 3.0 \text{ V, } V_{\text{OUT}} = 1.8 \text{ V} \\ &V_{\text{PP}} = 200 \text{ mV modulation} \\ &I_{\text{OUT}} = 1 \text{ mA, } C_{\text{OUT}} = 10 \mu\text{F} \end{aligned}$ | f = 100 kHz | PSRR | | 60 | | dB |
| Output Noise Voltage | | Vout = 1.8 V, lout = 50 mA f = 200 Hz to 100 kHz, C _{OUT} = 10 μF | | | 95 | | μV _{rms} |
| Thermal Shutdown Temperature (Note 14) | Temperature increasing from T _J = +25°C | | T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 14) | Temperature falling fro | m T _{SD} | T _{SDH} | _ | 15 | _ | °C |

 ^{13.} Not characterized at V_{IN} = 3.0 V, V_{OUT} = 1.8 V, I_{OUT} = 50 mA
 14. Guaranteed by design and characterization.
 15. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 16. Respect SOA.

ELECTRICAL CHARACTERISTICS – Voltage Version 2.1 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 3.1V$; $I_{OUT} = 1$ mA, $C_{IN} = C_{OUT} = 1.0$ μF , unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 19)

| Parameter | Test Conditions | Test Conditions | | Min | Тур | Max | Unit |
|--|---|---|---------------------|-------|-----|-------|---------------|
| Operating Input Voltage | 0 < I _{OUT} < 50 mA | 0 < I _{OUT} < 50 mA | | 3.1 | | 24 | V |
| Output Voltage Accuracy | 3.1 V < V _{IN} < 24 V, 0 < I _{OU} | _T < 50 mA | V _{OUT} | 2.058 | 2.1 | 2.142 | V |
| Line Regulation | 3.1 V ≤ VIN ≤ 24 V, I _{OUT} | = 1 mA | Reg _{LINE} | | 3 | 45 | mV |
| | 3.3 V ≤ VIN ≤ 24 V, I _{OUT} | = 1 mA | | | 3 | 10 | |
| Load Regulation | I _{OUT} = 0 mA to 50 r | nA | Reg _{LOAD} | | 10 | 15 | mV |
| Dropout Voltage (Note 17) | | | | | | | mV |
| Maximum Output Current | (Note 20) | (Note 20) | | 100 | | 200 | mA |
| Ground Current | 0 < I _{OUT} < 50 mA, V _{IN} : | = 24 V | I _{GND} | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $\begin{aligned} &V_{\text{IN}} = 3.1 \text{ V, } V_{\text{OUT}} = 2.1 \text{ V} \\ &V_{\text{PP}} = 200 \text{ mV modulation} \\ &I_{\text{OUT}} = 1 \text{ mA, } C_{\text{OUT}} = 10 \mu\text{F} \end{aligned}$ | f = 100 kHz | PSRR | | 60 | | dB |
| Output Noise Voltage | | Vout = 2.1 V, lout = 50 mA f = 200 Hz to 100 kHz, C _{OUT} = 10 μF | | | 105 | | μV_{rms} |
| Thermal Shutdown Temperature (Note 18) | Temperature increasing from T _J = +25°C | | T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 18) | Temperature falling from | m T _{SD} | T _{SDH} | _ | 15 | - | °C |

^{17.} Not characterized at V_{IN} = 3.1 V, V_{OUT} = 2.1 V, I_{OUT} = 50 mA

18. Guaranteed by design and characterization.

19. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 20. Respect SOA.

ELECTRICAL CHARACTERISTICS – Voltage Version 2.5 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 3.5 \text{ V}$; $I_{OUT} = 1 \text{ mA}$, $C_{IN} = C_{OUT} = 1.0 \ \mu\text{F}$, unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 23)

| Parameter | Test Conditions | | Symbol | Min | Тур | Max | Unit |
|--|---|---------|---------------------|------|-----|------|---------------|
| Operating Input Voltage | 0 < I _{OUT} < 50 mA | | V_{IN} | 3.5 | | 24 | V |
| Output Voltage Accuracy | 3.5 V < V _{IN} < 24 V, 0 < I _{OUT} < 5 | 50 mA | V _{OUT} | 2.45 | 2.5 | 2.55 | V |
| Line Regulation | V _{OUT} + 1 V ≤ V _{IN} ≤ 24 V, I _{OUT} = | = 1 mA | Reg _{LINE} | | 3 | 10 | mV |
| Load Regulation | I _{OUT} = 0 mA to 50 mA | | Reg _{LOAD} | | 10 | 15 | mV |
| Dropout Voltage (Note 21) | $V_{DO} = V_{IN} - (V_{OUT(NOM)} - 125 \text{ mV})$ $I_{OUT} = 50 \text{ mA}$ | | V_{DO} | | 260 | 450 | mV |
| Maximum Output Current | (Note 24) | | l _{OUT} | 100 | | 200 | mA |
| Ground Current | 0 < I _{OUT} < 50 mA, Vin = 24 | ١V | I_{GND} | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $\begin{array}{c} \text{VIN} = 3.5 \text{ V}, \text{ V}_{OUT} = 2.5 \text{ V} \\ \text{VPP} = 200 \text{ mV modulation} \\ \text{I}_{OUT} = 1 \text{ mA, C}_{OUT} = 10 \mu\text{F} \end{array}$ | 100 kHz | PSRR | | 60 | | dB |
| Output Noise Voltage | V_{OUT} = 2.5 V, I_{OUT} = 50 mA f = 200 Hz to 100 kHz, C_{OUT} = 10 μF | | V_N | | 115 | | μV_{rms} |
| Thermal Shutdown Temperature (Note 22) | Temperature increasing from T _J = +25°C | | T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 22) | Temperature falling from T ₅ | SD | T _{SDH} | _ | 15 | - | °C |

^{21.} Characterized when V_{OUT} falls 125 mV below the regulated voltage and only for devices with V_{OUT} = 2.5 V. 22. Guaranteed by design and characterization.

 ^{23.} Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 24. Respect SOA.

ELECTRICAL CHARACTERISTICS - Voltage Version 3.0 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 4.0 \text{ V}$; $I_{OUT} = 1 \text{ mA}$, $C_{IN} = C_{OUT} = 1.0 \ \mu\text{F}$, unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 27)

| Parameter | Test Conditions | Symbol | Min | Тур | Max | Unit |
|--|--|---------------------|------|-----|------|---------------|
| Operating Input Voltage | 0 < I _{OUT} < 50 mA | Vin | 4.0 | | 24 | V |
| Output Voltage Accuracy | 4.0 V < V _{IN} < 24 V, 0< I _{OUT} < 50 mA | Vouт | 2.94 | 3.0 | 3.06 | V |
| Line Regulation | $V_{OUT} + 1 V \le V_{IN} \le 24 V, I_{OUT} = 1 mA$ | Reg _{LINE} | | 3 | 10 | mV |
| Load Regulation | I _{OUT} = 0 mA to 50 mA | Reg _{LOAD} | | 10 | 15 | mV |
| Dropout voltage (Note 25) | $V_{DO} = V_{IN} - (V_{OUT(NOM)} - 150 \text{ mV})$ $I_{OUT} = 50 \text{ mA}$ | VDO | | 250 | 400 | mV |
| Maximum Output Current | (Note 28) | Іоит | 100 | | 200 | mA |
| Ground current | 0 < IOUT < 50 mA, VIN = 24 V | IGND | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $ \begin{array}{c} V_{IN} = 4.0 \text{ V}, V_{OUT} = 3.0 \text{ V} \\ V_{PP} = 100 \text{ mV modulation} \\ I_{OUT} = 1 \text{ mA}, C_{OUT} = 10 \mu\text{F} \end{array} $ | lz PSRR | | 60 | | dB |
| Output Noise Voltage | $V_{OUT} = 3 \text{ V, } I_{OUT} = 50 \text{ mA,}$ f = 200 Hz to 100 kHz, $C_{OUT} = 10 \mu\text{F}$ | Vn | | 135 | | μV_{rms} |
| Thermal Shutdown Temperature (Note 26) | Temperature increasing from T _J = +25°(| C TSD | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 26) | Temperature falling from T _{SD} | Тѕрн | - | 25 | - | °C |

^{25.} Characterized when VouT falls 150 mV below the regulated voltage and only for devices with VouT = 3.0 V

^{26.} Guaranteed by design and characterization.

^{27.} Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 28. Respect SOA

ELECTRICAL CHARACTERISTICS - Voltage Version 3.3 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 4.3 \text{ V}$; $I_{OUT} = 1 \text{ mA}$, $C_{IN} = C_{OUT} = 1.0 \ \mu\text{F}$, unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 31)

| Parameter | Test Conditions | Symbol | Min | Тур | Max | Unit |
|--|---|---------------------|-------|-----|-------|---------------|
| Operating Input Voltage | 0 < I _{OUT} < 50 mA | V _{IN} | 4.3 | | 24 | V |
| Output Voltage Accuracy | 4.3 V < V _{IN} < 24 V, 0 < I _{OUT} < 50 mA | V _{OUT} | 3.234 | 3.3 | 3.366 | V |
| Line Regulation | $V_{OUT} + 1 \text{ V} \le V_{IN} \le 24 \text{ V}, I_{OUT} = 1 \text{ mA}$ | Reg _{LINE} | | 3 | 10 | mV |
| Load Regulation | I _{OUT} = 0 mA to 50 mA | Reg _{LOAD} | | 10 | 15 | mV |
| Dropout Voltage (Note 29) | VDO = VIN - (VOUT(NOM) - 165 mV) IOUT = 50 mA | V _{DO} | | 230 | 350 | mV |
| Maximum Output Current | (Note 32) | I _{OUT} | 100 | | 200 | mA |
| Ground Current | 0 < IOUT < 50 mA, VIN = 24 V | I _{GND} | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $\begin{array}{c} V_{IN} = 4.3 \text{ V}, \ V_{OUT} = 3.3 \text{ V} \\ V_{PP} = 200 \text{ mV modulation} \\ I_{OUT} = 1 \text{ mA, } C_{OUT} = 10 \ \mu\text{F} \end{array}$ | lz PSRR | | 60 | | dB |
| Output Noise Voltage | Vout = 4.3 V, lout = 50 mA f = 200 Hz to 100 kHz, C_{OUT} = 10 μF | V _N | | 140 | | μV_{rms} |
| Thermal Shutdown Temperature (Note 30) | Temperature increasing from T _J = +25° | C T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 30) | Temperature falling from T _{SD} | T _{SDH} | - | 15 | - | °C |

^{29.} Characterized when VouT falls 165 mV below the regulated voltage and only for devices with VouT = 3.3 V.

^{30.} Guaranteed by design and characterization.

^{31.} Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

^{32.} Respect SOA.

ELECTRICAL CHARACTERISTICS – Voltage Version 5.0 V

 $-40^{\circ}C \le T_{J} \le 125^{\circ}C$; $V_{IN} = 6.0 \text{ V}$; $I_{OUT} = 1 \text{ mA}$, $C_{IN} = C_{OUT} = 1 \mu\text{F}$, unless otherwise noted. Typical values are at $T_{J} = +25^{\circ}C$. (Note 35)

| Parameter | Test Conditions | Test Conditions | | Min | Тур | Max | Unit |
|--|---|--|---------------------|-----|-----|-----|---------------|
| Operating Input Voltage | 0 < IOUT < 50 mA | 0 < IOUT < 50 mA | | 6.0 | | 24 | V |
| Output Voltage Accuracy | 6.0V < VIN < 24V, 0< IOUT | < 50 mA | V _{OUT} | 4.9 | 5.0 | 5.1 | V |
| Line Regulation | Vout + 1 V ≤ Vin ≤ 24 V, Io | out = 1mA | Reg _{LINE} | | 3 | 10 | mV |
| Load Regulation | IOUT = 0 mA to 50 r | mA | Reg _{LOAD} | | 10 | 15 | mV |
| Dropout Voltage (Note 33) | VDO = VIN - (VOUT(NOM) - IOUT = 50 mA | VDO = VIN - (VOUT(NOM) - 250 mV) IOUT = 50 mA | | | 230 | 350 | mV |
| Maximum Output Current | (Note 36) | (Note 36) | | 90 | | 200 | mA |
| Ground Current | 0 < IOUT < 50 mA, Vin: | = 24 V | I _{GND} | | 3.4 | 5.8 | μΑ |
| Power Supply Rejection Ratio | $\begin{array}{c} \text{Vin} = 6.0 \text{ V}, \text{ Vout} = 5.0 \text{ V} \\ \text{Vpp} = 200 \text{ mV modulation} \\ \text{Iout} = 1 \text{ mA}, C_{OUT} = 10 \mu\text{F} \end{array}$ | f = 100 kHz | PSRR | | 56 | | dB |
| Output Noise Voltage | Vout = 5.0 V, lout = 5 f = 200 Hz to 100 kHz, C _{OI} | | V _N | | 190 | | μV_{rms} |
| Thermal Shutdown Temperature (Note 34) | Temperature increasing from T _J = +25°C | | T _{SD} | | 170 | | °C |
| Thermal Shutdown Hysteresis (Note 34) | Temperature falling fro | m T _{SD} | T _{SDH} | _ | 15 | _ | °C |

^{33.} Characterized when VouT falls 250 mV below the regulated voltage and only for devices with VouT = 5.0 V.

^{34.} Guaranteed by design and characterization.

^{35.} Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

^{36.} Respect SOA.

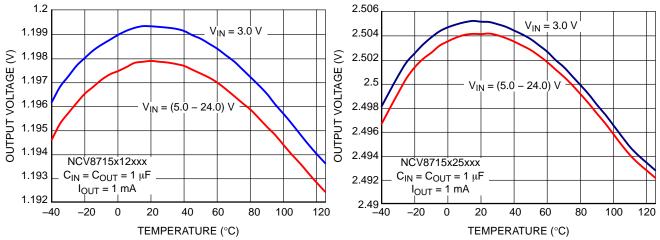


Figure 4. Output Voltage vs. Temperature

Figure 5. Output Voltage vs. Temperature

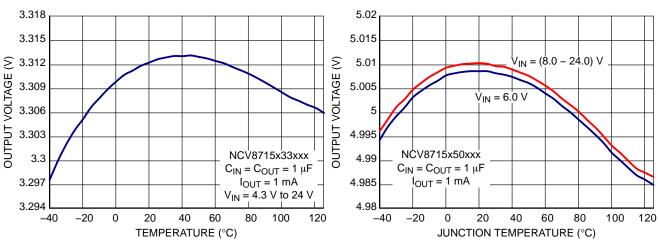


Figure 6. Output Voltage vs. Temperature

Figure 7. Output Voltage vs. Temperature

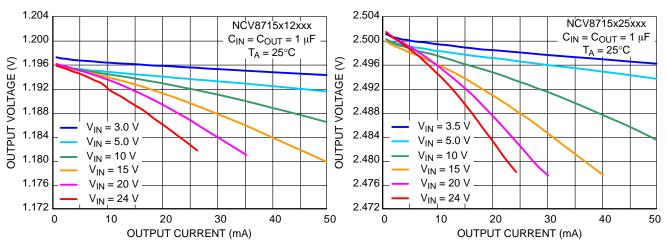


Figure 8. Output Voltage vs. Output Current

Figure 9. Output Voltage vs. Output Current

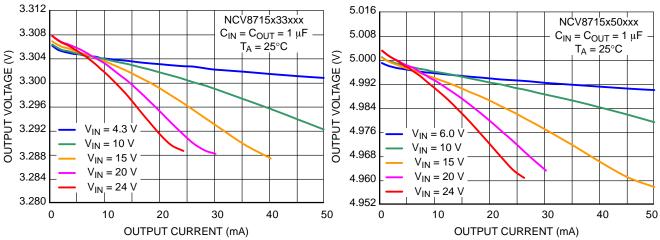


Figure 10. Output Voltage vs. Output Current

Figure 11. Output Voltage vs. Output Current

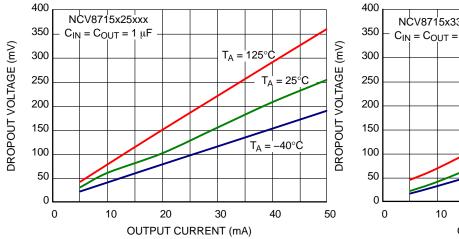


Figure 12. Dropout Voltage vs. Output Current

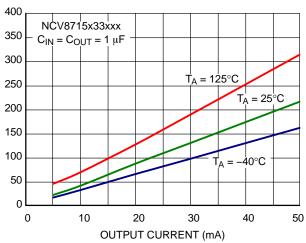


Figure 13. Dropout Voltage vs. Output Current

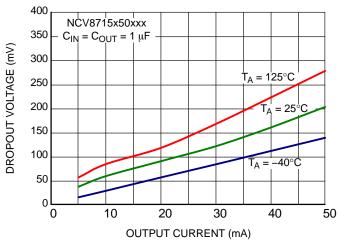


Figure 14. Dropout Voltage vs. Output Current

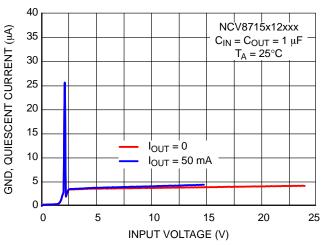


Figure 15. Ground Current vs. Input Voltage

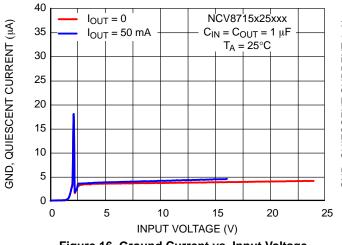


Figure 16. Ground Current vs. Input Voltage

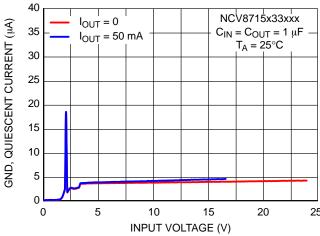


Figure 17. Ground Current vs. Input Voltage

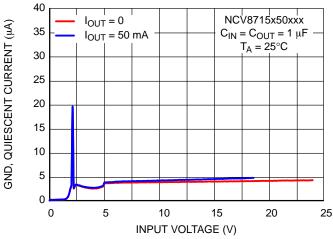


Figure 18. Ground Current vs. Input Voltage

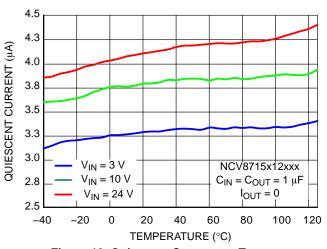


Figure 19. Quiescent Current vs. Temperature

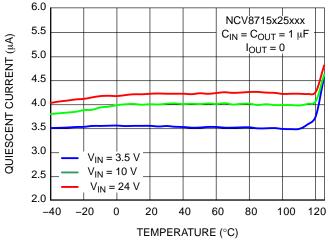


Figure 20. Quiescent Current vs. Temperature

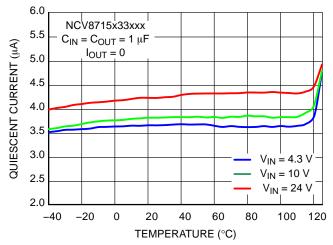


Figure 21. Quiescent Current vs. Temperature

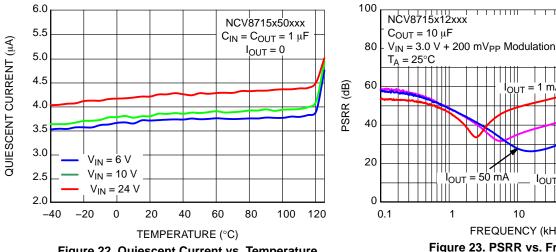
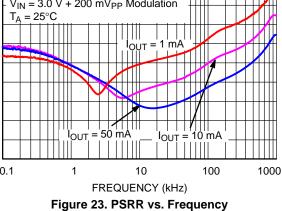


Figure 22. Quiescent Current vs. Temperature



1000

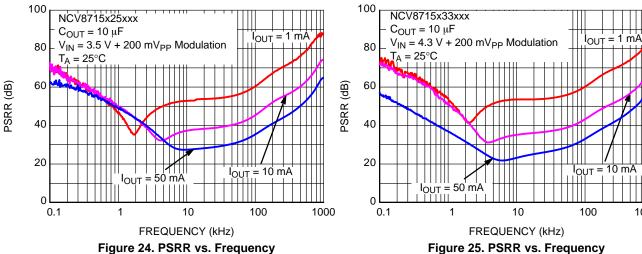


Figure 24. PSRR vs. Frequency

100

80

60

40

20

0 0.1

PSRR (dB)

NCV8715x50xxx

 $V_{IN} = 6.0 \text{ V} + 200 \text{ mV}_{PP} \text{ Modulation}$

 $C_{OUT} = 10 \mu F$

T_A = 25°C

1.6 $C_{OUT} = 10 \mu F$, 65.1 $\mu Vrms @ 200 Hz - 100 kHz$ OUTPUT VOLTAGE NOISE (μV/√Hz) C_{OUT} = 4.7 μ F, 80.5 μ Vrms @ 200 Hz – 100 kHz 1.4 C_{OUT} = 2.2 μ F, 111.5 μ Vrms @ 200 Hz - 100 kHz 1.2 $C_{OUT} = 1.0 \mu F$, 172.1 $\mu Vrms @ 200 Hz - 100 kHz$ 1.0 0.8 0.6 0.4 /8715x12xx $I_{OUT} = 50 \text{ mA}$ 0.2 T_A = 25°C $V_{IN} = 3 V$ 0.0 0.01 0.1 10 1000 100 FREQUENCY (kHz)

FREQUENCY (kHz) Figure 26. PSRR vs. Frequency

10

I_{OUT} = 50 mA

Figure 27. Output Spectral Noise Density vs. Frequency

1000

= 10 mA

100

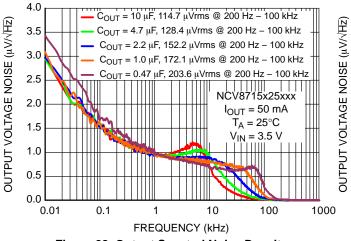


Figure 28. Output Spectral Noise Density vs. Frequency

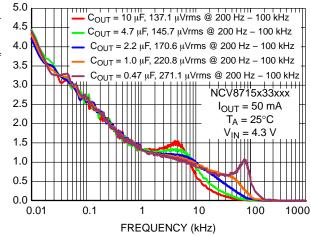


Figure 29. Output Spectral Noise Density vs. Frequency

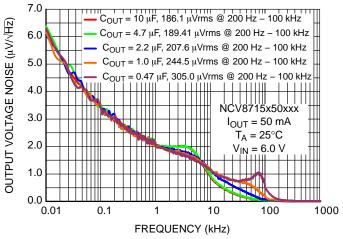


Figure 30. Output Spectral Noise Density vs. Frequency

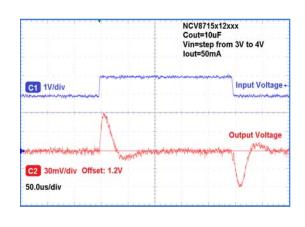


Figure 31. Line Transient Response

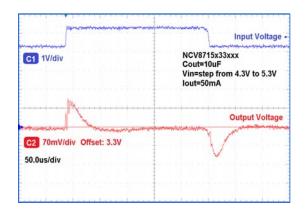


Figure 32. Line Transient Response

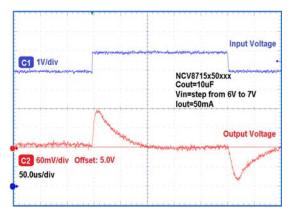
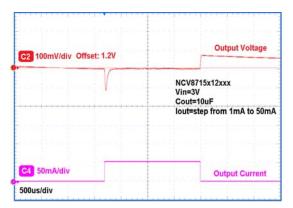


Figure 33. Line Transient Response





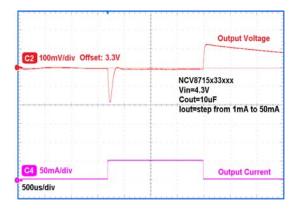


Figure 35. Load Transient Response

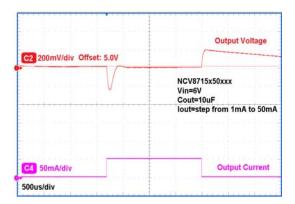


Figure 36. Load Transient Response

APPLICATIONS INFORMATION

The NCV8715 is the member of new family of Wide Input Voltage Range Low Dropout Regulators which delivers Ultra Low Ground Current consumption, Good Noise and Power Supply Rejection Ratio Performance.

Input Decoupling (C_{IN})

It is recommended to connect at least $0.1~\mu F$ Ceramic X5R or X7R capacitor between IN and GND pin of the device. This capacitor will provide a low impedance path for any unwanted AC signals or Noise superimposed onto constant Input Voltage. The good input capacitor will limit the influence of input trace inductances and source resistance during sudden load current changes.

Higher capacitance and lower ESR Capacitors will improve the overall line transient response.

Output Decoupling (COUT)

The NCV8715 does not require a minimum Equivalent Series Resistance (ESR) for the output capacitor. The device is designed to be stable with standard ceramics capacitors with values of 0.47 μF or greater up to 10 μF . The X5R and X7R types have the lowest capacitance variations over temperature thus they are recommended.

Power Dissipation and Heat sinking

The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part. The maximum power dissipation the NCV8715 can handle is given by:

$$P_{D(MAX)} = \frac{\left[T_{J(MAX)} - T_{A}\right]}{R_{A \mid A}}$$
 (eq. 1)

The power dissipated by the NCV8715 for given application conditions can be calculated from the following equations:

$$P_D \approx V_{IN}(I_{GND}(I_{OUT})) + I_{OUT}(V_{IN} - V_{OUT})$$
 (eq. 2)

or

$$V_{IN(MAX)} \approx \frac{P_{D(MAX)} + (V_{OUT} \times I_{OUT})}{I_{OUT} + I_{GND}}$$
 (eq. 3)

Hints

VIN and GND printed circuit board traces should be as wide as possible. When the impedance of these traces is high, there is a chance to pick up noise or cause the regulator to malfunction. Place external components, especially the output capacitor, as close as possible to the NCV8715, and make traces as short as possible.

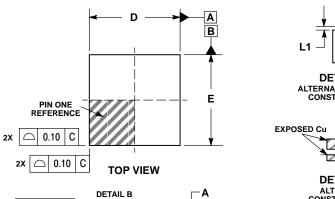
ORDERING INFORMATION

| Device | Nominal Output Voltage | Marking | Package | Shipping [†] | | | | |
|----------------|---------------------------|------------|---------------------|-----------------------|--|--|--|--|
| NCV8715SQ12T2G | 1.2 V | V5A | | | | | | |
| NCV8715SQ15T2G | 1.5 V | V5C | | | | | | |
| NCV8715SQ18T2G | 1.8 V | V5D | | | | | | |
| NCV8715SQ21T2G | 2.1 V | V5J | SC-88A/SC-70 | | | | | |
| NCV8715SQ25T2G | 2.5 V | V5E | (Pb-Free)* | | | | | |
| NCV8715SQ30T2G | 3.0 V | V5F V5G | | | | | | |
| NCV8715SQ33T2G | 3.3 V | | | | | | | |
| NCV8715SQ50T2G | 5.0 V | V5H | | 3000 / Tape & Reel | | | | |
| NCV8715MX12TBG | 1.2 V | VA | | | | | | |
| NCV8715MX15TBG | 1.5 V | VC | | | | | | |
| NCV8715MX18TBG | 1.8 V | VE | | | | | | |
| NCV8715MX25TBG | 2.5 V | VE | XDFN6 (Pb-Free)* | | | | | |
| NCV8715MX30TBG | 3.0 V | VF | (| | | | | |
| NCV8715MX33TBG | 3.3 V | VG | | | | | | |
| NCV8715MX50TBG | 5.0 V | VH | | | | | | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

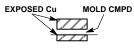
PACKAGE DIMENSIONS

XDFN6 1.5x1.5, 0.5P CASE 711AE ISSUE A





DETAIL A ALTERNATE TERMINAL CONSTRUCTIONS

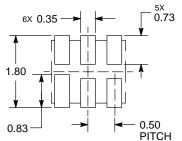


DETAIL B ALTERNATE CONSTRUCTIONS

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.10 AND 0.20mm FROM TERMINAL TIP.

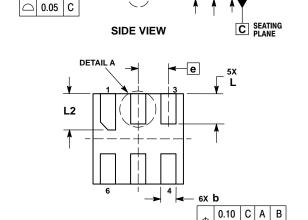
| | MILLIMETERS | | | |
|-----|-------------|------|--|--|
| DIM | MIN | MAX | | |
| Α | 0.35 | 0.45 | | |
| A1 | 0.00 | 0.05 | | |
| A3 | 0.13 REF | | | |
| b | 0.20 | 0.30 | | |
| D | 1.50 BSC | | | |
| E | 1.50 BSC | | | |
| е | 0.50 BSC | | | |
| L | 0.40 | 0.60 | | |
| L1 | | 0.15 | | |
| L2 | 0.50 | 0.70 | | |

RECOMMENDED MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



BOTTOM VIEW

С 0.05

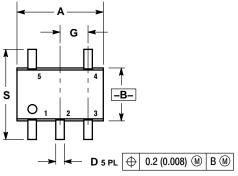
NOTE 3

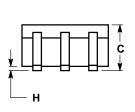
0.05 C

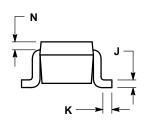
PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353)

CASE 419A-02 **ISSUE L**







NOTES:

- NOTES:

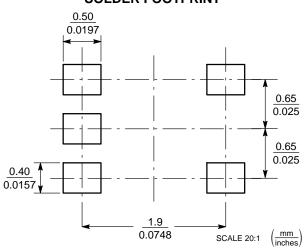
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. 419A-01 OBSOLETE. NEW STANDARD
- HISA-02.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE

| | INC | HES | MILLIMETERS | |
|-----|-----------|-------|-------------|------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.071 | 0.087 | 1.80 | 2.20 |
| В | 0.045 | 0.053 | 1.15 | 1.35 |
| С | 0.031 | 0.043 | 0.80 | 1.10 |
| D | 0.004 | 0.012 | 0.10 | 0.30 |
| G | 0.026 BSC | | 0.65 BSC | |
| Н | | 0.004 | | 0.10 |
| J | 0.004 | 0.010 | 0.10 | 0.25 |
| K | 0.004 | 0.012 | 0.10 | 0.30 |
| N | 0.008 REF | | 0.20 REF | |
| S | 0.079 | 0.087 | 2.00 | 2.20 |

SOLDER FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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